

SPECIALIST DETECTORS FOR NUCLEAR PHYSICS

SILICON DETECTOR TYPE:	POSITION SENSITIVE DETECTOR (PSD)
TECHNOLOGY:	3 INCH SILICON
DESIGN:	Ion implanted totally depleted sensitive resistor division detector incorporating equipotential strips for high linearity and excellent position resolution.
ACTIVE AREA:	1.44 cm ² AA1 = 12 x 12 mm ² AA2 = 13 x 13 mm ²
TOTAL LEAKAGE CURRENT:	5 µA typically, 50 µA maximum
OPERATING VOLTAGE:	FD to FD + 30 V
FULL DEPLETION (FD):	10 – 1000 V subject to thickness selected
INTER ANODE RESISTANCE:	3 KΩ minimum, 10 KΩ maximum
POSITION RESOLUTION:	200 µm
ALPHA RESOLUTION:	0.3 % typically, 1 % maximum
THICKNESS:	60 µm, 140 µm, 300 µm, 500 µm and 1000 µm
THICKNESS TOLERANCE:	± 10 µm
THICKNESS UNIFORMITY:	± 5 µm
METALLISATION:	3000 Å
METALLISATION TOLERANCE:	± 1000 Å
PACKAGES:	PCB with metal housing
CONNECTOR OPTIONS:	SMA, SMB, Conhex or Microdot
STACKING	Design compatible for stacking with E detectors.

QUALITY ASSURANCE :ISO9001

